



WBFBP-02C Plastic-Encapsulate Diodes

DSS70LED02 Schottky barrier diode

DESCRIPTION

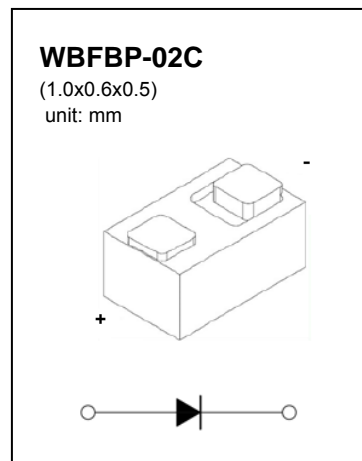
Planar Schottky barrier diode with an integrated guard ring for stress protection.

FEATURES

- Low diode capacitance
- Low forward voltage
- Guard ring protected
- High breakdown voltage
- Power dissipation comparable to SOT-23

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Mobile communication ,digital (still) cameras , PDAs and PCMCIA cards



MARKING: S5

Maximum ratings (T_a=25°C unless otherwise noted)

Parameter	Symbol	Limits	Unit
DC Reverse Voltage	V _R	70	V
Continuous Forward Current	I _F	70	mA
Non-Repetitive Peak Forward Current(t _p <10ms)	I _{FSM}	100	mA
Power Dissipation	P _D	250	mW
Thermal Resistance from Junction to Ambient	R _{θJA}	400	°C/W
Junction Temperature	T _J	125	°C
Storage Temperature	T _{stg}	-55~+150	°C

Electrical characteristics (T_a=25°C unless otherwise noted)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Continuous forward voltage	V_F			410	mV	I _F =1mA
				750		I _F =10mA
				1000		I _F =15mA
Continuous reverse current*	I_R			100	nA	V _R =50V
				500		V _R =70V
Diode capacitance	C_d			2	pF	V _R =0V, f=1MHz

*Pulse Test: Pulse width=300μs;Duty cycle=0.02.